

COMPLEMENTARY SILICON POWER TRANSISTORS

The MJ15003 and MJ15004 are power base power transistors designed for high power audio, disk head positioners, linear amplifiers, switching regulators, and other linear applications.

NPN	PNP
MJ15003	MJ15004

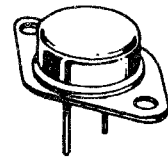
FEATURES:

- * High Power Dissipation
 $P_D = 250 \text{ W } (T_C = 25^\circ\text{C})$
- * High DC Current Gain and Low Saturation Voltage
 $hFE = 25(\text{Min}) @ I_C = 5.0 \text{ A}, V_{CE} = 2.0 \text{ V}$
- * For Low Distortion Complementary Designs

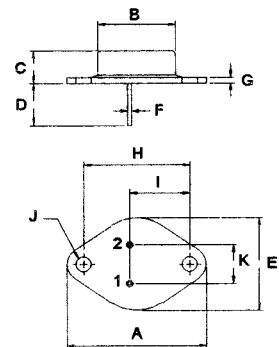
20 AMPERE
 COMPLEMENTARY SILICON
 POWER TRANSISTORS
 140 VOLTS
 250 WATTS

MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CE(SUS)}$	140	V
Collector-Base Voltage	V_{CBO}	140	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current-Continuous Peak (1)	I_C I_{CM}	20 30	A
Base Current-Continuous Peak (1)	I_B I_{BM}	5.0 10	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	250 1.43	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-65 to +200	$^\circ\text{C}$



TO-3



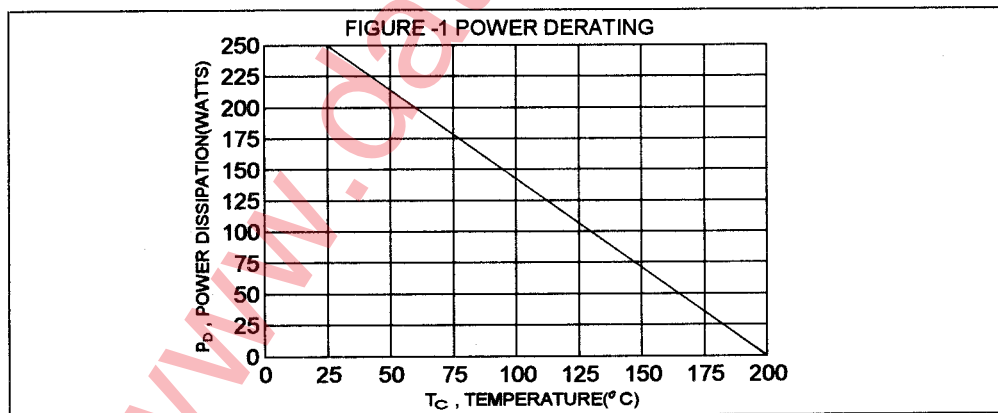
PIN 1. BASE
 2. EMITTER
 COLLECTOR (CASE)

(1) Pulse Test: Pulse width = 5 ms, Duty Cycle < 10%

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	0.70	$^\circ\text{C/W}$

DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18



ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector - Emitter Sustaining Voltage (2) ($I_C = 200\text{ mA}$, $I_B = 0$)	$V_{CEO(sus)}$	140		V
Collector Cutoff Current ($V_{CE} = 140\text{ V}$, $I_B = 0$)	I_{CO}		250	μA
Collector Cutoff Current ($V_{CE} = 140\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$) ($V_{CE} = 140\text{ V}$, $V_{BE(off)} = 1.5\text{ V}$, $T_C = 150^\circ\text{C}$)	I_{CEX}		100 2.0	μA mA
Emitter Cutoff Current ($V_{EB} = 5.0\text{ V}$, $I_C = 0$)	I_{EBO}		100	μA

ON CHARACTERISTICS (2)

DC Current Gain ($I_C = 5.0\text{ A}$, $V_{CE} = 2.0\text{ V}$)	hFE	25	150	
Collector - Emitter Saturation Voltage ($I_C = 5.0\text{ A}$, $I_B = 500\text{ mA}$)	$V_{CE(sat)}$		1.0	V
Base - Emitter On Voltage ($I_C = 5.0\text{ A}$, $V_{CE} = 2.0\text{ V}$)	$V_{BE(on)}$		2.0	V

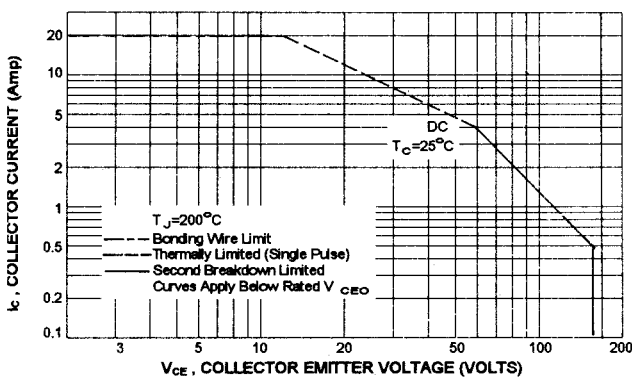
DYNAMIC CHARACTERISTICS

Current Gain - Bandwidth Product (3) ($I_C = 500\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 0.5\text{ MHz}$)	f_T	2.0		MHz
Output capacitance ($V_{CB} = 4.0\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$)	C_{ob}		1000	pF

(2) Pulse Test: Pulse width = $300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

(3) $f_T = |h_{fe}| \cdot f_{test}$

FIG-2 FORWARD BIAS SAFE OPERATING AREA



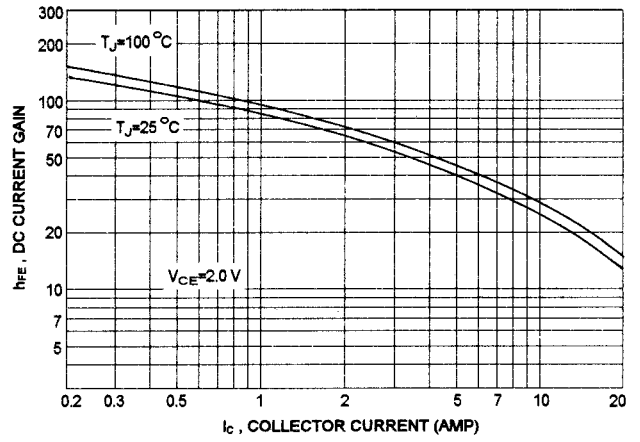
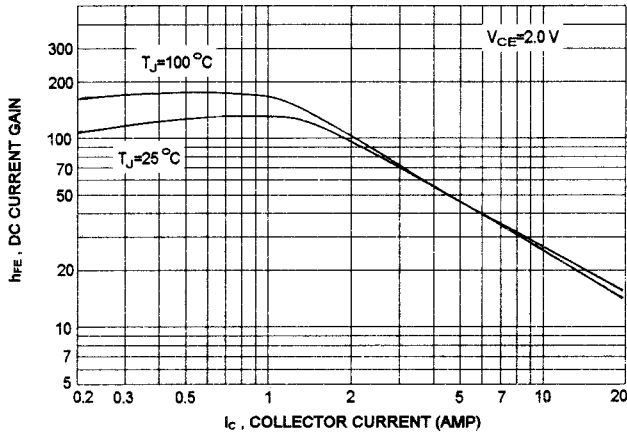
There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of FIG-2 is base on $T_{J(pk)}=200^\circ\text{C}$; T_C is variable depending on conditions. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MJ15003

DC CURRENT GAIN

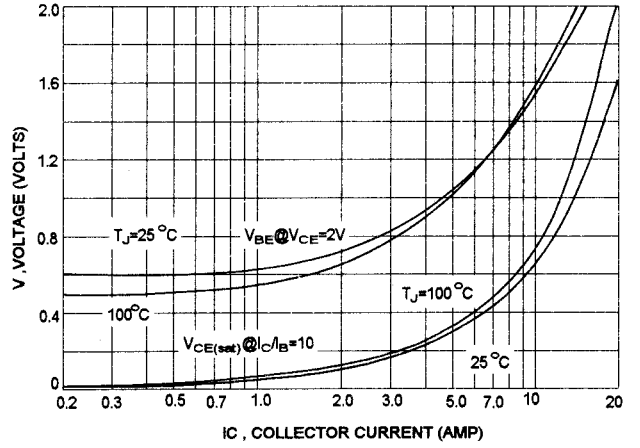
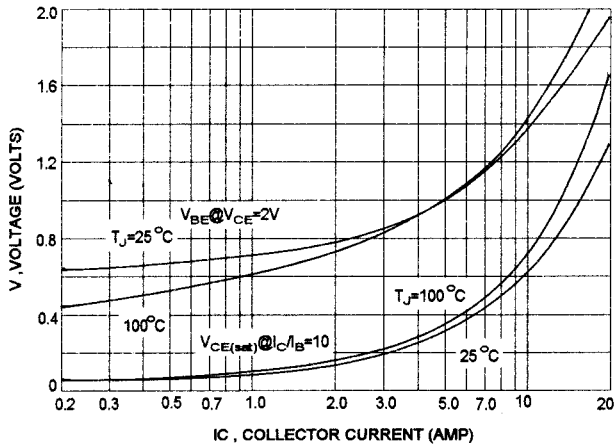
MJ15004



"ON" VOLTAGE

MJ15003

MJ15004



CAPACITANCES

CURRENT GAIN- BANDWIDTH PRODUCT

